

SoftBank Corp. Subsidiary SAIMEMORY and Intel Collaborate to Commercialize Next-generation Memory Technology

Companies jointly advancing research and development with aim of commercialization in FY2029

SoftBank Corp. (“SoftBank”) announced its wholly owned subsidiary SAIMEMORY Corp. (“SAIMEMORY”) signed a collaborative agreement with Intel Corporation (“Intel”) on February 2, 2026 to advance the commercialization of Z-Angle Memory (ZAM), a next-generation memory technology designed for high capacity, high bandwidth and low power consumption.

Established in December 2024, SAIMEMORY is a SoftBank subsidiary conducting research and development to promote the commercialization of next-generation memory technologies. SAIMEMORY will leverage the next-generation memory foundational technologies and technical expertise validated by Intel’s Next Generation DRAM Bonding (NGDB) initiative*2 that was completed under the Advanced Memory Technology (AMT) program*1 managed by the U.S. Department of Energy and National Nuclear Security Administration through the Sandia National Laboratory, Lawrence Livermore National Laboratory and Los Alamos National Laboratory. With the aim of creating prototypes in the fiscal year ending March 31, 2028 (FY2027) and achieving commercialization in FY2029, SAIMEMORY will advance research and development on innovative memory architectures and manufacturing technologies. Through the utilization of ZAM next-generation memory technology, SAIMEMORY and Intel will work together to enable high-capacity and high-bandwidth data processing, enhanced processing performance and reduced power consumption in data centers and other environments that require the training and inference of large-scale AI models.

SAIMEMORY’s development of next-generation memory technologies represents one of SoftBank’s key initiatives to support next-generation social infrastructure. By collaborating with Intel and other technology partners and research institutions in Japan and abroad, SoftBank will contribute to the creation of advanced, homegrown semiconductor technologies, and to the strengthening of Japan’s global competitiveness.

*1 AMT program: supported by the U.S. Department of Energy, the AMT program is a research program that aims to establish foundational technologies for next-generation memory.

*2 NGDB initiative: a technology development initiative led by Intel, aimed at significantly improving the performance and power efficiency of next-generation DRAM (high-speed memory used as the main memory in computers and servers).